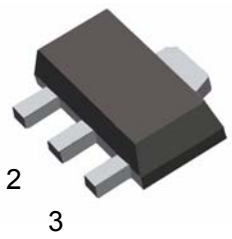
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO.,LTD

SOT-89 Plastic-Encapsulate Transistors

PXT8550 TRANSISTOR (PNP)

SOT-89

1. BASE
2. COLLECTOR
3. EMITTER



FEATURES

Compliment to PXT8050

MARKING: Y2

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-1.5	A
P_C	Collector Power Dissipation	0.5	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

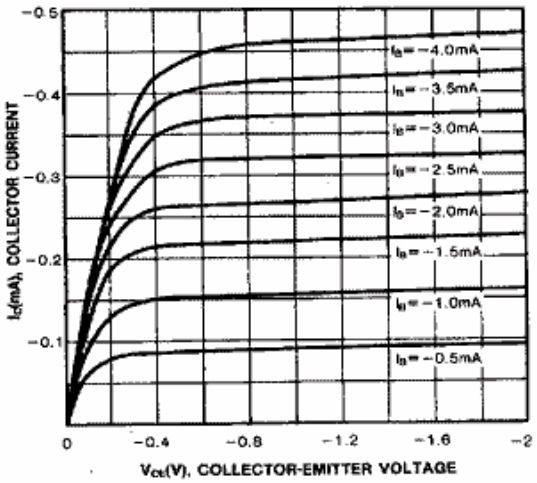
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= -100μA, I_E=0	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= -0.1mA, I_B=0	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -100μA, I_C=0	-5		V
Collector cut-off current	I_{CBO}	V_{CB}= -40 V,I_E=0		-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}= -20V, I_B=0		-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V, I_C=0		-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}= -1V, I_C= -100mA	85	400	
	$h_{FE(2)}$	V_{CE}= -1V, I_C= -800mA	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-800mA, I_B= -80mA		-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-800mA, I_B= -80mA		-1.2	V
Base-emitter on voltage	$V_{BE(on)}$	Ic=-1V,V_{CE}=-10mA		-1	V
Base-emitter positive favor voltage	V_{BEF}	I_B=-1A		-1.55	V
Transition frequency	f_T	V_{CE}= -10V, I_C= -50mA	100		MHz
output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz		20	pF

CLASSIFICATION OF $h_{FE(1)}$

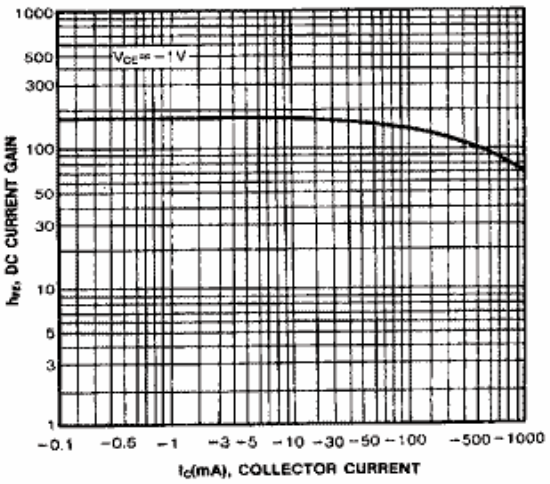
Rank	B	C	D	D3
Range	85-160	120-200	160-300	300-400

Typical characteristics PXT8550

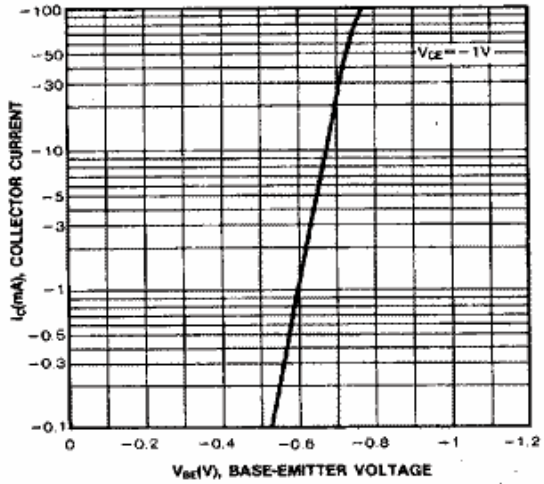
STATIC CHARACTERISTIC



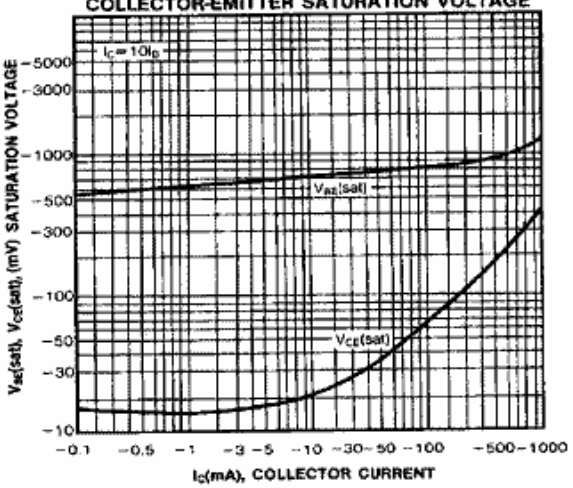
DC CURRENT GAIN



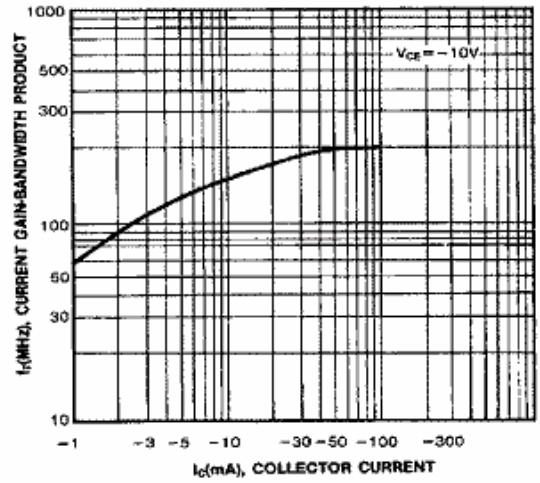
BASE-EMITTER ON VOLTAGE



BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



CURRENT GAIN-BANDWIDTH PRODUCT



COLLECTOR OUTPUT CAPACITANCE